

30V/4.5A N-Channel MOSFET

Product Summary

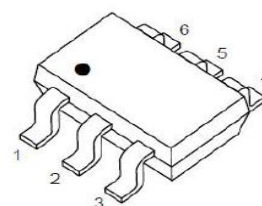
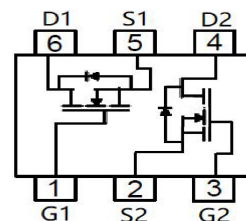
V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
30V	45mΩ@10V	4.5A
	55mΩ@4.5V	

Features

- N-channel, normal level
- Very low on-resistance $R_{DS(on)}$

Application

- Industrial power supplies
- Boost converters
- Rectifier
- Telecom
- Battery management system



SOT23-6L

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±12	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 4.5V ¹	4.5	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, V_{GS} @ 4.5V ¹	2.8	A
I_{DM}	Pulsed Drain Current ²	15	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ³	1.25	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	--	-	°C/W

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.6	1.0	1.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =10V, I _D =4A	-	30	45	mΩ
		V _{GS} =4.5V, I _D =3A	-	45	55	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	233	-	pF
C _{oss}	Output Capacitance		-	44	-	pF
C _{rss}	Reverse Transfer Capacitance		-	33	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =2A, V _{GS} =10V	-	3	-	nC
Q _{gs}	Gate-Source Charge		-	0.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	0.8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =4A, R _{GEN} =3Ω, V _{GS} =10V	-	4	-	ns
t _r	Turn-on Rise Time		-	2.1	-	ns
t _{d(off)}	Turn-off Delay Time		-	15	-	ns
t _f	Turn-off Fall Time		-	3.2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	4.5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =4A	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

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Typical Performance Characteristics

Figure 1: Output Characteristics

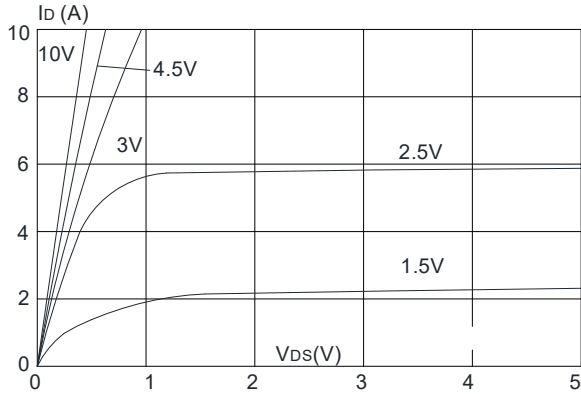


Figure 2: Typical Transfer Characteristics

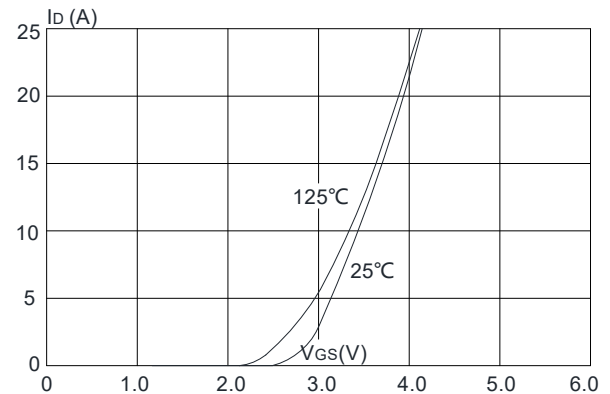


Figure 3: On-resistance vs. Drain Current

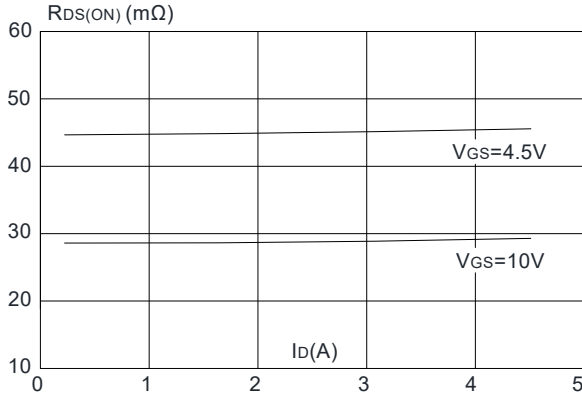


Figure 4: Body Diode Characteristics

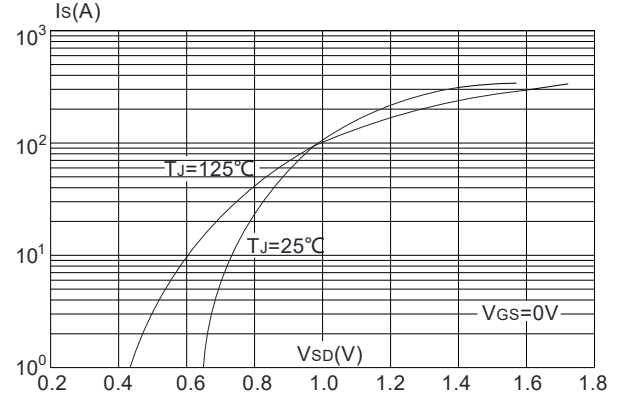


Figure 5: Gate Charge Characteristics

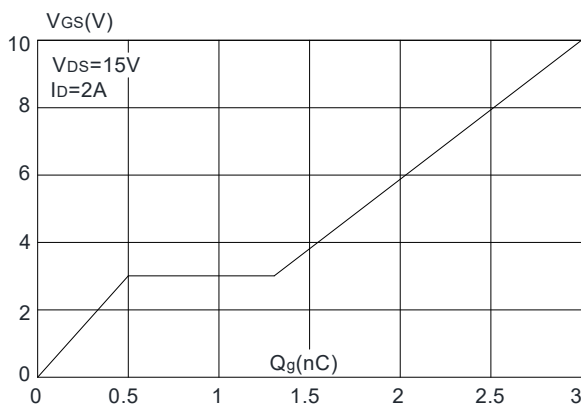
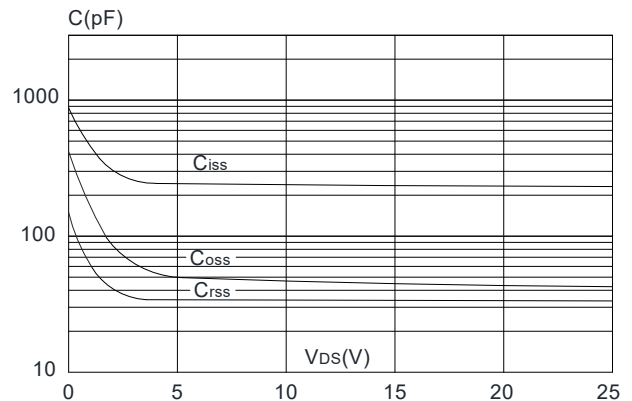


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

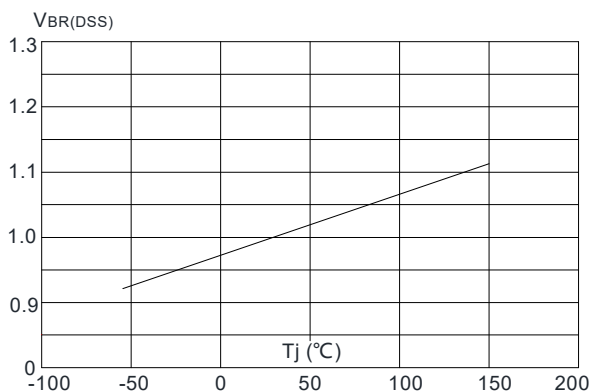


Figure 8: Normalized on Resistance vs. Junction Temperature

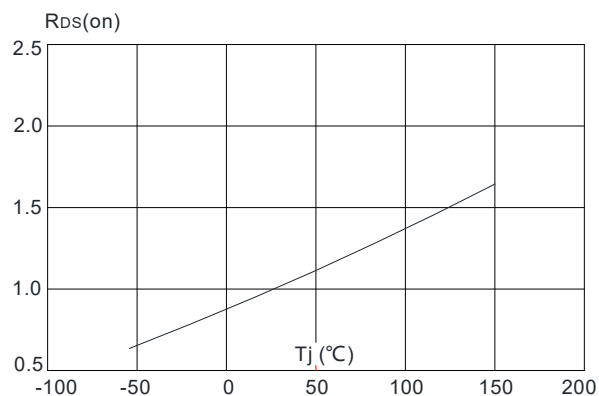


Figure 9: Maximum Safe Operating Area

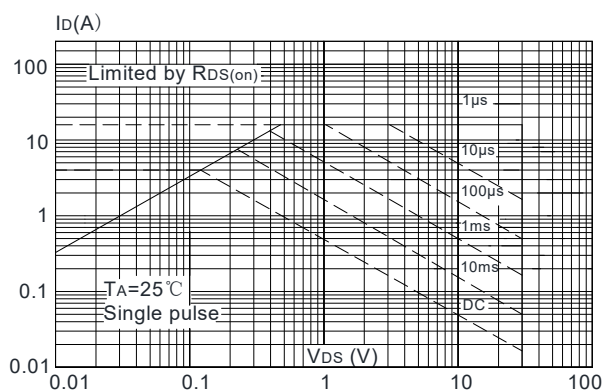


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

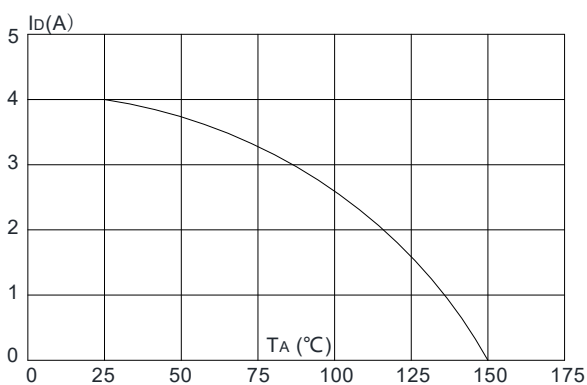
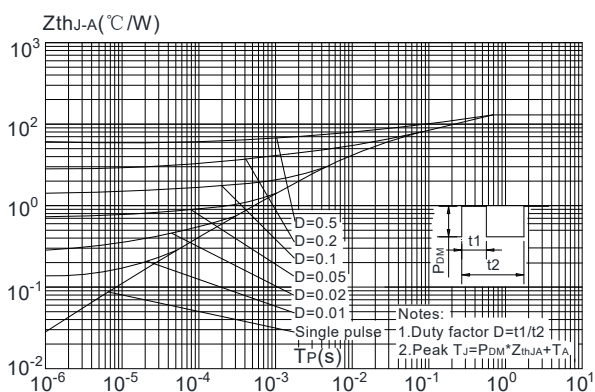
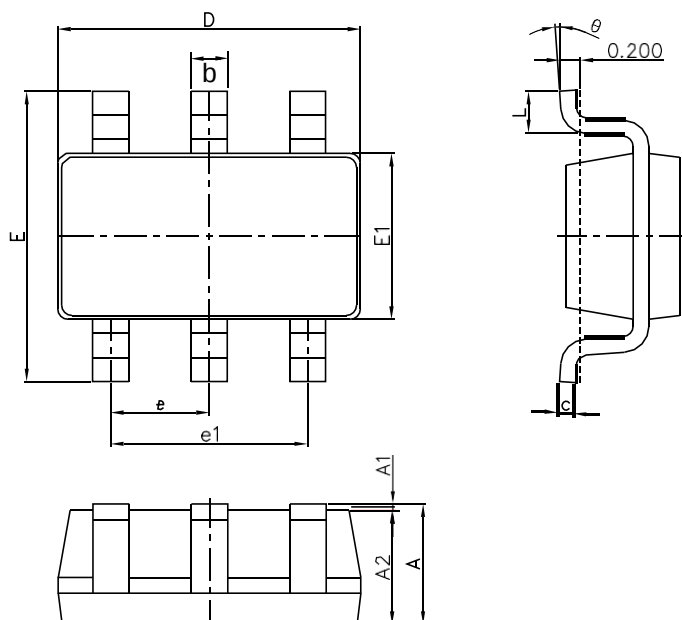
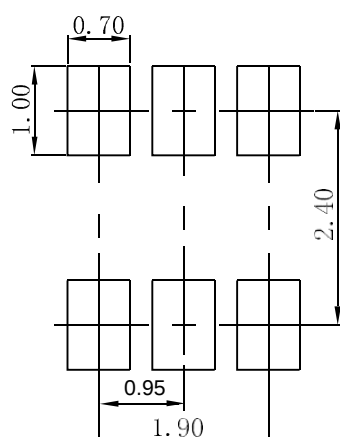


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



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SOT-23-6L Package Outline Dimensions


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

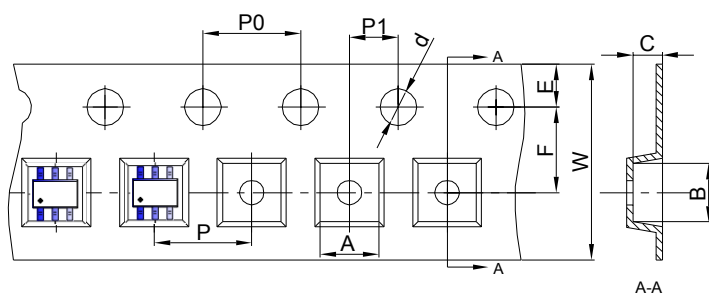
SOT-23-6L Suggested Pad Layout


Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

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SOT-23-6L Embossed Carrier Tape



Packaging Description:

SOT-26L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOT-23-6L	3.17	3.23	1.37	Ø1.55	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23-6L Tape Leader and Trailer

